

NPN BLACK PLASTIC PHOTOTRANSISTOR

Part Number: L-610MP4BT/BD

Features

- •MECHANICALLY AND SPECTRALLY MATCHED

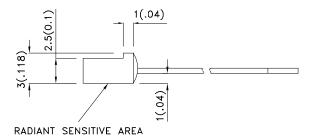
 TO THE KM-4457 INFRARED EMITTING LED

 LAMP SERIES
- •BLACK DIFFUSED LENS.
- •COUPLED WITH KM-4457 INFRARED EMITTING LED LAMP SERIES FOR MOUSE APPLICATION.
- •RoHS COMPLIANT.

Description

Made with NPN silicon phototransistor chips.

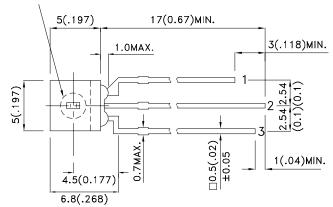
Package Dimensions

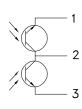


1 EMITTER (PTR A)

2 COLLECTOR (COM)

3 EMITTER (PTR B)





Notes

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25 (0.01")$ unless otherwise noted.
- 3. Lead spacing is measured where the leads emerge from the package.
- 4. Specifications are subject to change without notice.





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APPROVED: WYNEC CHECKED: Allen Liu DRAWN: S.J.LIU

Kingbright

Electrical / Optical Characteristics at Ta=25°C

Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30	-	-	V	Ic=100uA Ee=0mW/cm ²
VBR ECO	Emitter-to-Collector Breakdown Voltage	5	-	-	V	IE=100uA Ee=0mW/cm ²
VCE (SAT)	Collector-to-Emitter Saturation Voltage	-	-	0.4	V	Ic=500uA Ee=5mW/cm ²
ICEO	Collector Dark Current	-	-	100	nA	VCE=10V Ee=0mW/cm ²
Tr	Rise Time (10% to 90%)	-	16	-	us	VCE = 5V IC=1mA RL=1000Ω
TF	Fall Time (90% to 10%)	-	18	-	us	
I(ON)	On State Collector Current	0.1	0.5	-	mA	$VCE = 5V$ $Ee=1mW/cm^{2}$ $\lambda=940nm$
R	Collector Current Ratio of 2 Phototransistor	0.8	1	1.25		Ic (on) (a)/ Ic(on) (b)

Absolute Maximum Ratings at Ta=25°C

Parameter	Max.Ratings		
Collector-to-Emitter Voltage	30V		
Emitter-to-Collector Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating Temperature Range	-55°C ~ +100°C		
Storage Temperature Range	-55°C ~ +100°C		
Lead Solder Temperature (>5mm for 5sec)	260°C		

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